Abstracts

Reliability Study on Pseudomorphic InGaAs Power HEMT Devices at 60 GHz

C.H. Chen, Y. Saito, H.C. Yen, K. Tan, G. Onak and J. Mancini. "Reliability Study on Pseudomorphic InGaAs Power HEMT Devices at 60 GHz." 1994 MTT-S International Microwave Symposium Digest 94.2 (1994 Vol. II [MWSYM]): 817-820.

Two-temperature RF-stressed accelerated life test on discrete pseudomorphic InGaAs power HEMT devices at 60 GHz shows a failure mode with an activation energy of 1.6 eV. The projected mean time-to-failure of 1 E7 hours at 125° C channel temperature indicates that this device technology can be highly reliable for critical applications at millimeter-wave frequencies.

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